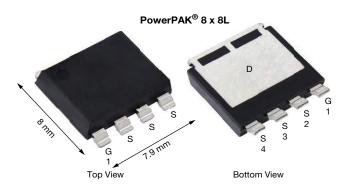
# SQJQ144AE

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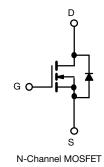
# Automotive N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V <sub>DS</sub> (V)	40
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.0009
I <sub>D</sub> (A)	575
Configuration	Single
Package	PowerPAK 8 x 8L

#### FEATURES

- TrenchFET<sup>®</sup> Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Thin 1.6 mm package
- Very low thermal resistance
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ABSOLUTE MAXIMUM RATINGS (	T <sub>C</sub> = 25 °C, unles	s otherwise noted	(k	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	40	V
Gate-source voltage		V <sub>GS</sub>	± 20	v
Continuous drain current	T <sub>C</sub> = 25 °C	I-	575	
Continuous drain current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	330	
Continuous source current (diode conduction)		I <sub>S</sub>	545	А
Pulsed drain current <sup>a</sup>	I <sub>DM</sub>	1800		
Single pulse avalanche current		I <sub>AS</sub>	60	
Single pulse avalanche energy		E <sub>AS</sub>	180	mJ
Maximum power dissipation	T <sub>C</sub> = 25 °C 600		W	
Maximum power dissipation	T <sub>C</sub> = 125 °C	FD	200	vv
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Soldering recommendations (peak temperature)	С		260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount <sup>b</sup>	R <sub>thJA</sub>	44	°C/W
Junction-to-case (drain)		R <sub>thJC</sub>	0.25	C/W

#### Notes

c. See solder profile (<u>www.vishay.com/doc?73257</u>). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. When mounted on 1" square PCB (FR4 material)

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<b>SPECIFICATIONS</b> ( $T_C = 25$ °C	C, unless othe	erwise noted)						
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static	•				•	•	•	
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 µA	40	-	-	v	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2	3	3.5	v	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, $V_{GS} = \pm 20 V$	-	-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1		
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	150	1	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	100	-	-	Α	
		$V_{GS} = 10 V$	I <sub>D</sub> = 20 A	-	0.0007	0.0009		
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 V$	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	-	-	0.0015	Ω	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	-	-	0.0019	1	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 60 A	-	160	-	S	
Dynamic <sup>b</sup>	•	•			•	•	•	
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 25 V, f = 1 MHz	-	7220	9020	pF	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	2290	2860		
Reverse transfer capacitance	C <sub>rss</sub>			-	175	220		
Total gate charge <sup>c</sup>	Qg			-	116	145	nC	
Gate-source charge c	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 20 \text{ V}, \text{ I}_{D} = 30 \text{ A}$	-	36	-		
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	25	-		
Gate resistance	R <sub>g</sub>		f = 1 MHz	0.9	1.6	2.6	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	17	27	- ns	
Rise time <sup>c</sup>	tr	V <sub>DD</sub> =	20 V, $R_1 = 0.66 \Omega$	-	27	41		
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>		$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	41	62		
Fall time <sup>c</sup>	t <sub>f</sub>			-	18	27	1	
Source-Drain Diode Ratings and Ch	aracteristics <sup>b</sup>							
Reverse recovery time	t <sub>rr</sub>			-	66	-	ns	
Reverse recovery charge	Q <sub>rr</sub>		= 32 V, I <sub>FM</sub> = 15 A, /dt = 100 A/µs	-	94	-	nC	
Reverse recovery current	I <sub>RM</sub>		/αι = 100 Αγμ5	-	-	-3.6	Α	
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	1600	Α	
Forward voltage	V <sub>SD</sub>	IF :	= 50 A, V <sub>GS</sub> = 0	-	0.8	1.1	V	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing

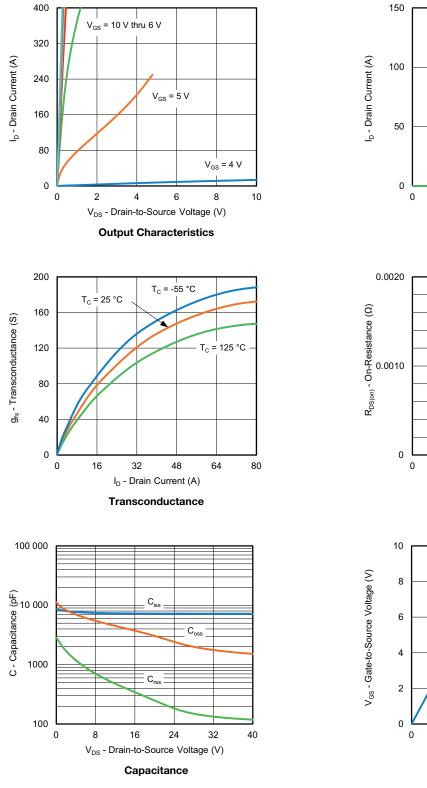
c. Independent of operating temperature

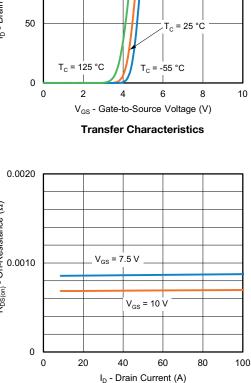
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

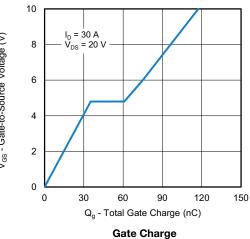


## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)





**On-Resistance vs. Drain Current** 



S22-0228-Rev. E, 14-Mar-2022

3

Document Number: 77170

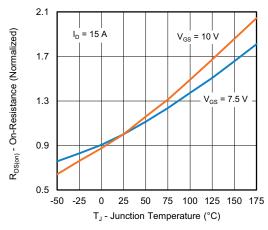
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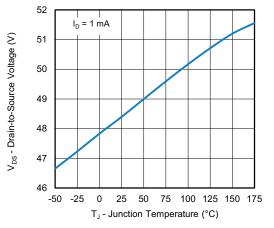
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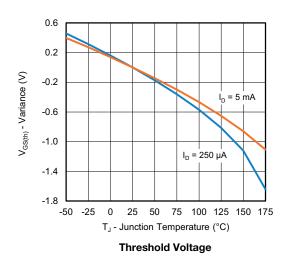
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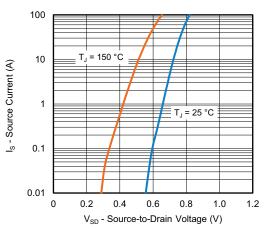


**On-Resistance vs. Junction Temperature** 

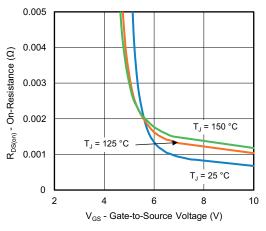


Drain Source Breakdown vs. Junction Temperature

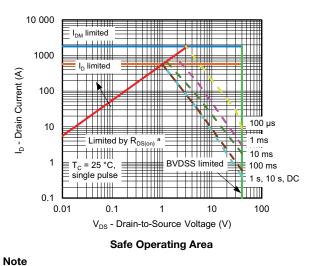




Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



a.  $V_{GS}$  > minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

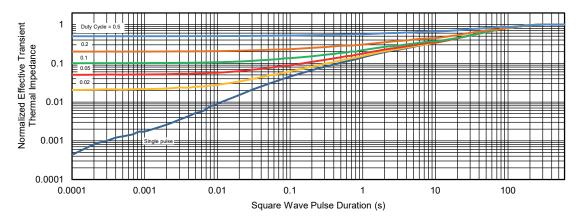
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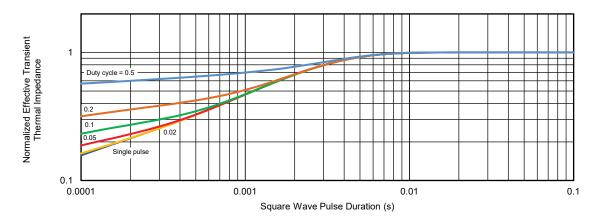
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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

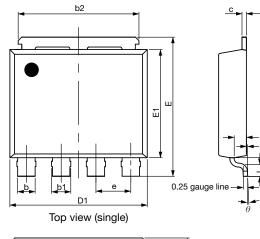


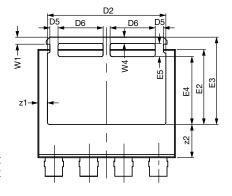
Normalized Thermal Transient Impedance, Junction-to-Case

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# PowerPAK<sup>®</sup> 8 x 8L BWL Case Outline 2

A1





Bottom view (single)

1						_ <b>↑</b>
F	-		-	-	A.	<
l	_					

		MILLIMETERS			INCHES	
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	1.50	1.60	1.70	0.059	0.063	0.067
A1	0.00	-	0.127	0.000	-	0.005
A2	0.655	0.705	0.755	0.026	0.028	0.030
b	0.92	1.00	1.08	0.036	0.039	0.043
b1	1.02	1.10	1.18	0.040	0.043	0.046
b2	6.84	6.94	7.04	0.269	0.273	0.277
С	0.20	0.25	0.30	0.008	0.010	0.012
D1	7.80	7.90	8.00	0.307	0.311	0.315
D2	6.70	6.80	6.90	0.264	0.268	0.272
D5	0.37	0.47	0.57	0.015	0.019	0.022
D6	2.49	2.59	2.69	0.098	0.102	0.106
е	1.97	2.00	2.03	0.078	0.079	0.080
Е	7.90	8.00	8.10	0.311	0.315	0.319
E1	6.12	6.22	6.32	0.241	0.245	0.249
E2	4.21	4.31	4.41	0.166	0.170	0.174
E3	4.92	5.02	5.12	0.194	0.198	0.202
E4	3.80	3.90	4.00	0.150	0.154	0.157
E5	0.65	0.75	0.85	0.026	0.030	0.033
L	0.61	0.68	0.75	0.024	0.027	0.030
L1	1.00	1.07	1.15	0.039	0.042	0.045
W1	0.30	0.40	0.50	0.012	0.016	0.020
W4	0.32	0.37	0.42	0.013	0.015	0.017
z1	0.45	0.55	0.65	0.018	0.022	0.026
z2	1.81	1.91	2.01	0.071	0.075	0.079
θ	0°	-	5°	0°	-	5°
N: S19-0643-F G: 6073	lev. B, 05-Aug-2019					

#### Note

• Millimeter will govern

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